GP 2813

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Gurtej Singh Sandhu et al.

Title: METHOD TO REDUCE FIXED CHARGE IN CVD OZONE DEPOSITED FILMS

Docket No.: 303.573US1
Filed: April 22, 1996
Examiner: Matthew Wipple

Serial No.: 08/636,069
Due Date: September 15, 1999
Group Art Unit: 2813

Assistant Commissioner for Patents
Washington, D.C. 20231

We are transmitting herewith the following attached items (as indicated with an "X"):

X A return postcard.
X An Amendment and Response (6 Pages).

Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this Transmittal Letter and the paper, as described above, are being deposited in the United States Postal Service, as first class mail, in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on this 7 day of September, 1999.

By: Thomas W. Leffert
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(GENERAL)

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AMENDMENT AND RESPONSE

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9-29-99

Assistant Commissioner for Patents
Washington, D.C. 20231

Applicant has reviewed the Office Action mailed June 15, 1999. Please amend the application as follows:

IN THE CLAIMS

Please amend claims 31, 42, 51 and 52 as follows:

31. (Once amended) A method of depositing a silicon dioxide layer on a substrate surface, comprising:

contacting the substrate surface with a reaction volume of gas comprising a SiO_2 precursor and ozone; [and]

heating the substrate surface to a temperature of about 480°C to 700°C; and

illuminating the reaction volume of gas from a light source without directly exposing the substrate surface to the light source.

42. (Once amended) A method of depositing a doped silicon dioxide layer on a substrate surface, comprising:

contacting the substrate surface with a reaction volume of gas comprising a SiO_2 precursor, ozone and at least one dopant source; [and]

heating the substrate surface to a temperature of about 480°C to 700°C; and

illuminating the reaction volume of gas from a light source without directly exposing the substrate surface to the light source.